

isc N-Channel MOSFET Transistor

IRF530N
• FEATURES

- Low $R_{DS(on)}$
- V_{GS} Rated at $\pm 20V$
- Silicon Gate for Fast Switching Speed
- Rugged
- Low Drive Requirements

• DESCRIPTION

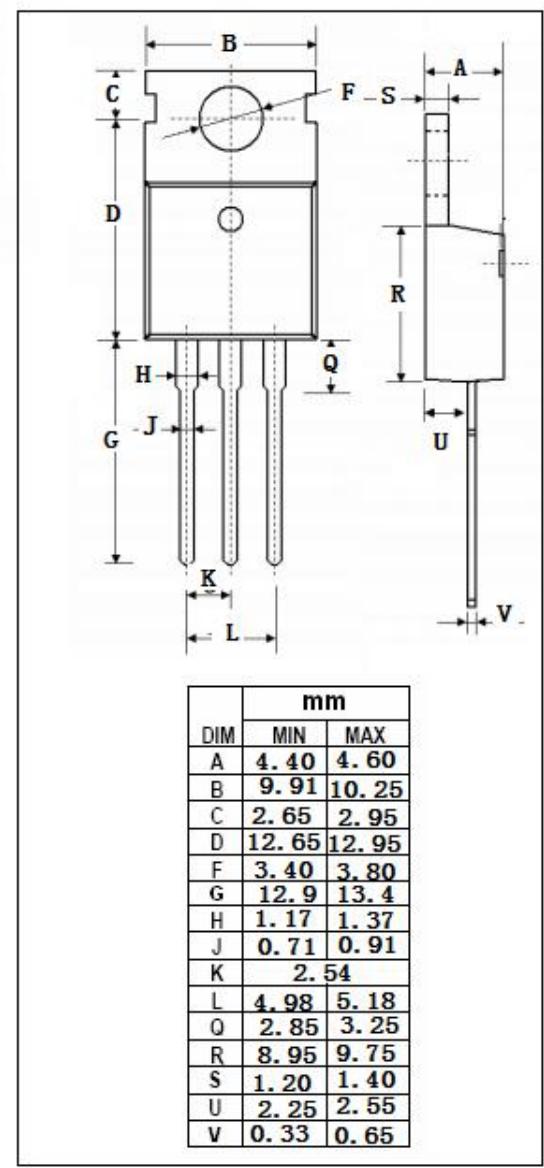
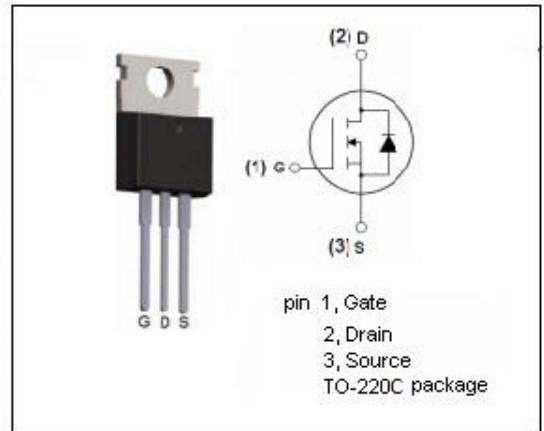
- Designed especially for high voltage,high speed applications, such as off-line switching power supplies , UPS,AC and DC motor controls,relay and solenoid drivers.

• ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage-Continuous	± 20	V
I_D	Drain Current-Continuous	17	A
I_{DM}	Drain Current-Single Plused	68	A
P_D	Total Dissipation @ $T_c=25^\circ C$	79	W
T_j	Max. Operating Junction Temperature	-55~175	$^\circ C$
T_{stg}	Storage Temperature	-55~175	$^\circ C$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance,Junction to Case	1.9	$^\circ C/W$
$R_{th\ j-a}$	Thermal Resistance,Junction to Ambient	60	$^\circ C/W$



isc N-Channel MOSFET Transistor**IRF530N****ELECTRICAL CHARACTERISTICS** $T_c=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0; I_D=0.25\text{mA}$	100			V
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}; I_D=1.0\text{mA}$	2		4	V
$R_{\text{DS}(\text{on})}$	Drain-Source On-Resistance	$V_{\text{GS}}=10\text{V}; I_D=9\text{A}$			0.11	Ω
I_{GSS}	Gate-Body Leakage Current	$V_{\text{GS}}=\pm 20\text{V}; V_{\text{DS}}=0$			± 100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{\text{DS}}=100\text{V}; V_{\text{GS}}=0$			10	μA
V_{SD}	Forward On-Voltage	$I_S=17\text{A}; V_{\text{GS}}=0$			1.2	V
C_{iss}	Input Capacitance	$V_{\text{DS}}=25\text{V}, V_{\text{GS}}=0\text{V}, F=1.0\text{MHz}$		633		pF
C_{oss}	Output Capacitance			103		pF
C_{rss}	Reverse Transfer Capacitance			61		pF

• SWITCHING CHARACTERISTICS ($T_c=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$T_{\text{d}(\text{on})}$	Turn-on Delay Time	$V_{\text{DD}}=50\text{V}$ $V_{\text{GS}}=10\text{V}$ $R_{\text{GS}}=2.7\Omega$ $R_{\text{GEN}}=5.6\Omega$		6		ns
T_r	Rise Time			36		ns
$T_{\text{d}(\text{off})}$	Turn-off Delay Time			18		ns
T_f	Fall Time			12		ns